

3-STATE Quad Buffers MM74HC125, MM74HC126

General Description

The MM74HC125 and MM74HC126 are general purpose 3–STATE high speed non–inverting buffers utilizing advanced silicon–gate CMOS technology. They have high drive current outputs which enable high speed operation even when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuitry, yet have speeds comparable to low power Schottky TTL circuits. Both circuits are capable of driving up to 15 low power Schottky inputs.

The MM74HC125 require the 3–STATE control input C to be taken high to put the output into the high impedance condition, whereas the MM74HC126 require the control input to be low to put the output into high impedance.

All inputs are protected from damage due to static discharge by diodes to VCC and ground.

Features

- Typical Propagation Delay: 13 ns
- Wide Operating Voltage Range: 2 V 6 V
- Low Input Current: 1 μA Maximum
- Low Quiescent Current: 160 µA maximum (74HC Series)
- Fanout of 15 LS-TTL Loads
- These Devices are Pb-Free, Halide Free and are RoHS Compliant

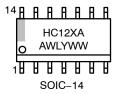


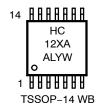


SOIC-14 CASE 751EF



MARKING DIAGRAM





HC12XA= Specific Device Code (X = 5 or 6)

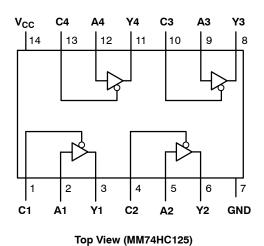
A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

Connection Diagram



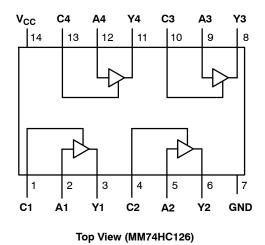


Figure 1. Pin Assignments for SOIC and TSSOP

TRUTH TABLE (MM74HC125)

Inp	Output	
Α	С	Υ
Н	L	Н
L	L	L
Х	Н	Z

TRUTH TABLE (MM74HC126)

Inp	Output	
Α	С	Υ
Н	Н	Н
L	Н	L
Х	L	Z

ABSOLUTE MAXIMUM RATINGS (Note 1)

Symbol		Parameter		
V _{CC}	Supply Voltage		−0.5 to +7.0 V	
V _{IN}	DC Input Voltage		–0.5 to V _{CC} + 0.5 V	
V _{OUT}	DC Output Voltage		–0.5 to V _{CC} + 0.5 V	
I _{IK} , I _{OK}	Clamp Diode Current	±20 mA		
l _{out}	DC Output Current, per Pin	35 mA		
I _{CC}	DC V _{CC} or GND Current, per Pin	±70 mA		
T _{STG}	Storage Temperature Range		–65°C to +150°C	
P_{D}	Power Dissipation Note 2		600 mW	
	S.O. Package Only		500 mW	
TL	Lead Temperature (Soldering 10 S	Seconds)	260°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Unless otherwise specified all voltages are referenced to ground.
- 2. Power Dissipation temperature derating plastic "N" package: –12 mW/°C from 65°C to 85°C.

RECOMMENDED OPERATING CONDITIONS

Symbol		Parameter			Unit
V _{CC}	Supply Voltage	Supply Voltage			
V _{IN} , V _{OUT}	DC Input or Output Voltage	OC Input or Output Voltage			
T _A	Operating Temperature Range			+125	°C
t _r , t _f	Input Rise or Fall Time V _{CC} = 2.0 V		-	1000	ns
		V _{CC} = 4.5 V	-	500	ns
		V _{CC} = 6.0 V	-	400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC CHARACTERISTICS (Note 3)

				T _A =	25°C	T _A = -40°C to 85°C	T _A = -55°C to 125°C	
Symbol	Parameter	Conditions	V _{CC} (V)	Тур	(Guaranteed Li	mits	Unit
V _{IH}	Minimum HIGH Level Input		2.0	-	1.5	1.5	1.5	V
	Voltage		4.5	-	3.15	3.15	3.15	
			6.0	-	4.2	4.2	4.2	
V_{IL}	Maximum LOW Level Input		2.0	-	0.5	0.5	0.5	٧
	Voltage		4.5	-	1.35	1.35	1.35	
			6.0	-	1.8	1.8	1.8	
V _{OH}	Minimum HIGH Level Output	$V_{IN} = V_{IH}$ or V_{IL} ,	2.0	2.0	1.9	1.9	1.9	V
	Voltage	I _{OUT} ≤ 20 μA	4.5	4.5	4.4	4.4	4.4	
			6.0	6.0	5.9	5.9	5.9	
		$V_{IN} = V_{IH} \text{ or } V_{IL},$ $ I_{OUT} \le 6.0 \text{ mA}$	4.5	4.2	3.98	3.84	3.7	
		$V_{IN} = V_{IH} \text{ or } V_{IL},$ $ I_{OUT} \le 7.8 \text{ mA}$	6.0	5.7	5.48	5.34	5.2	
V _{OL}	Maximum LOW Level Output	$V_{IN} = V_{IH}$ or V_{IL} ,	2.0	0	0.1	0.1	0.1	V
	Voltage	I _{OUT} ≤ 20 μA	4.5	0	0.1	0.1	0.1	
			6.0	0	0.1	0.1	0.1	
		$V_{IN} = V_{IH} \text{ or } V_{IL},$ $ I_{OUT} \le 6.0 \text{ mA}$	4.5	0.2	0.26	0.33	0.4	
		$V_{IN} = V_{IH} \text{ or } V_{IL},$ $ I_{OUT} \le 7.8 \text{ mA}$	6.0	0.2	0.26	0.33	0.4	
l _{OZ}	Maximum 3-STATE Output Leakage Current	$ \begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL}, \\ &V_{OUT} = V_{CC} \text{ or GND} \\ &C_n = \text{Disabled} \end{aligned} $	6.0	-	±0.5	±5	±10	μΑ
I _{IN}	Maximum Input Current	V _{IN} = V _{CC} or GND	6.0	-	±0.1	±1.0	±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND, $I_{OUT} = 0 \mu A$	6.0	-	8.0	80	160	μΑ

^{3.} For a power supply of 5 V $\pm 10\%$ the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5 V. Thus the 4.5 V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5 V and 4.5 V respectively. (The V_{IH} value at 5.5 V is 3.85 V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0 V values should be used.

AC CHARACTERISTICS (V $_{CC}$ = 5 V, T $_{A}$ = 25°C, C $_{L}$ = 45 pF, t $_{r}$ = t $_{f}$ = 6 ns)

Symbol	Parameter	Conditions	Тур	Guaranteed Limit	Unit
t _{PHL} , t _{PLH}	Maximum Propagation Delay Time		13	18	ns
t _{PZH}	Maximum Output Enable Time to HIGH Level	$R_L = 1 \text{ k}\Omega$	13	25	ns
t _{PHZ}	Maximum Output Disable Time from HIGH Level	$R_L = 1 \text{ k}\Omega$, $C_L = 5 \text{ pF}$	17	25	ns
t _{PZL}	Maximum Output Enable Time to LOW Level	$R_L = 1 \text{ k}\Omega$	18	25	ns
t _{PLZ}	Maximum Output Disable Time from LOW Level	$R_L = 1 \text{ k}\Omega$, $C_L = 5 \text{ pF}$	13	25	ns

AC CHARACTERISTICS (V_{CC} = 2.0 V to 6.0 V, C_L = 50 pF, t_r = t_f = 6 ns (unless otherwise specified))

				T _A =	25°C	T _A = -40°C to 85°C	T _A = -55°C to 125°C	
Symbol	Parameter	V _{CC} (V)	Conditions	Тур	G	iuaranteed Li	mits	Unit
t _{PHL} , t _{PLH}	Maximum Propagation Delay Time	2.0		40	100	125	150	ns
		4.5		14	20	25	30	
		6.0		12	17	21	25	
t _{PLH} , t _{PHL}	Maximum Propagation Delay Time	2.0	C _L = 150 pF,	35	130	163	195	ns
		4.5		14	26	33	39	
		6.0		12	22	28	39	
t _{PZH} , t _{PZL}	Maximum Output Enable Time	2.0	R _L = 1 kΩ	25	125	156	188	ns
		4.5		14	25	31	38	
		6.0		12	21	26	31	
t _{PHZ} , t _{PLZ}	Maximum Output Disable Time	2.0	R _L = 1 kΩ	25	125	156	188	ns
		4.5		14	25	31	38	
		6.0		12	21	26	31	
t _{PZL} , t _{PZH}	Maximum Output Enable Time	2.0	C _L = 150 pF,	35	140	175	210	ns
		4.5	$R_L = 1 \text{ k}\Omega$	15	28	35	42	
		6.0		13	24	30	36	
t _{TLH} , t _{THL}	Maximum Output Rise and Fall Time	2.0	C _L = 50 pF	30	60	75	90	ns
		4.5		7	12	15	18	
		6.0		6	10	13	15	
C _{IN}	Input Capacitance			5	10	10	10	pF
C _{OUT}	Output Capacitance Outputs			15	20	20	20	pF
C _{PD}	Power Dissipation Capacitance		Enabled	45	-	_	-	pF
	(per gate) (Note 4)		Disabled	6	-	-	-	

^{4.} C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} \ V_{CC}^2 \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC}$.

ORDERING INFORMATION

Part Number	Package	Shipping [†]
MM74HC125M	SOIC-14, Case 751A-03 (Pb-Free, Halide Free)	55 Units / Tube
MM74HC125MX	SOIC-14, Case 751A-03 (Pb-Free, Halide Free)	2500 / Tape & Reel
MM74HC125MTC	TSSOP-14, Case 948G-01 (Pb-Free, Halide Free)	96 Units / Tube
MM74HC125MTCX	TSSOP-14 WB, Case 948G-01 (Pb-Free, Halide Free)	2500 / Tape & Reel
MM74HC126M	SOIC-14, Case 751A-03 (Pb-Free, Halide Free)	55 Units / Tube
MM74HC126MX	SOIC-14, Case 751EF (Pb-Free, Halide Free)	2500 / Tape & Reel
MM74HC126MTCX	TSSOP-14 WB, Case 948G-01 (Pb-Free, Halide Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NOTE: Device also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering number.

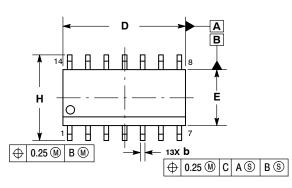


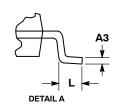


△ 0.10

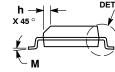
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016





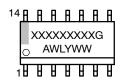




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE
 MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIN	IETERS	INC	HES
DIM	MIN MAX		MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
œ	1.27	BSC	0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7°

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code Α = Assembly Location

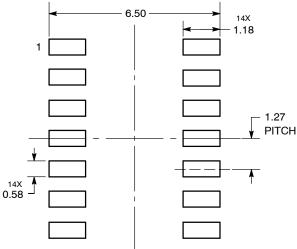
WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*

C SEATING PLANE

DIMENSIONS: MILLIMETERS



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Rep Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOIC-14 NB		PAGE 1 OF 2		

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

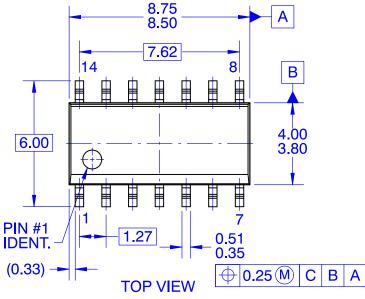
STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

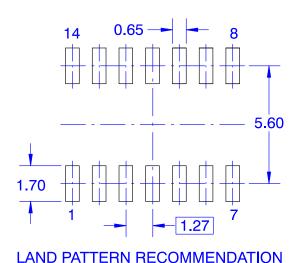
DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOIC-14 NB		PAGE 2 OF 2		

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

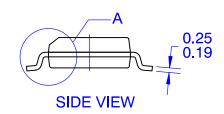
SOIC14 CASE 751EF ISSUE O

DATE 30 SEP 2016



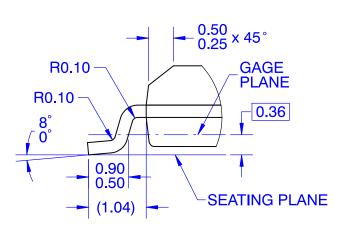


1.75 MAX 0.10 1.50 0.25 0.10 **FRONT VIEW**



NOTES:

- A. CONFORMS TO JEDEC MS-012, VARIATION AB, ISSUE C
 B. ALL DIMENSIONS ARE IN MILLIMETERS
- C. DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS
- LAND PATTERN STANDARD: SOIC127P600X145-14M
- E. CONFORMS TO ASME Y14.5M, 2009



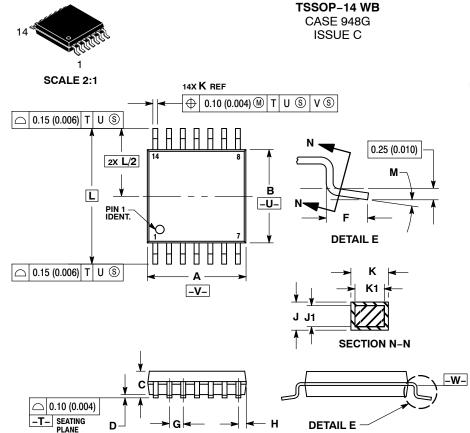
DETAIL A SCALE 16:1

DOCUMENT NUMBER:	98AON13739G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOIC14		PAGE 1 OF 1	

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

DATE 17 FEB 2016





- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

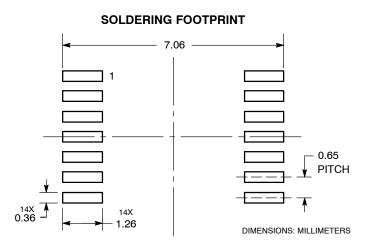
 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
м	o °	8 °	o °	8 °

GENERIC MARKING DIAGRAM*





= Assembly Location

= Wafer Lot V - Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location) *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASH70246A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TSSOP-14 WB		PAGE 1 OF 1	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.org/www.onsemi.or

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

